NSN 5961-01-467-6583

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-467-6583 **Inclosure Material:** Glass **Overall Length:** 30.000 millimeters **Terminal Length:** 12.600 millimeters **Overall Height:** 2.400 millimeters **Overall Width:** 5.100 millimeters **Mounting Facility Quantity: Mounting Method: Terminal Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 100.0 breakdown voltage, collector to emitter, sustained and 100.0 breakdown voltage, collector-to-base, emitter open **Current Rating Per Characteristic:** 100.00 nanoamperes forward current, average peak **Power Rating Per Characteristic:** 200.0 watts small-signal input power, common-emitter absolute **Maximum Operating Tempurature Per Measurement Point:** -65.0 degrees celsius case and 175.0 degrees celsius case **Special Features:** Hardness critical item **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: